



IMS 1605M: 64K x 1
IMS 1625M: 16K x 4
IMS 1629M: 16K x 4 with Output Enable
IMS 1626/7M: 16K x 4 with Separate I/Os
IMS 1635M: 8K x 8
IMS 1695M: 8K x 9

Advance Information

FEATURES

- INMOS' Very High Speed Double Metal CMOS
- Advanced Process-1.2 Micron Design Rules
- 64K Bit Devices
- 20, 25, and 35ns Address Access Times
- 20, 25 and 35 ns Chip Enable Access Times
- Fully TTL Compatible
- Single +5V ± 10% Operation
- Battery Backup Operation - 2V Data Retention, 10µA typical at 25°C
- Packages include: DIP and LCC

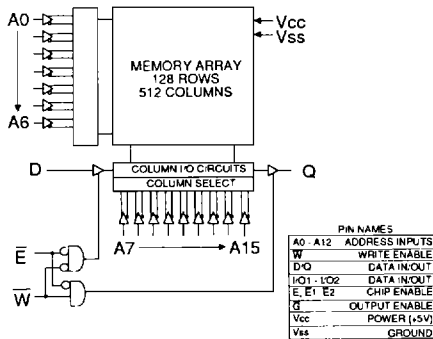
IMS16X5M series High Performance Memory Products MIL-STD-833C

DESCRIPTION

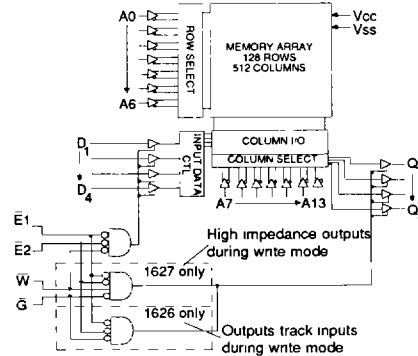
The INMOS IMS16X5M series are high speed advanced 64K double layer metal CMOS Static RAMs.

The range features fully static operation requiring no external clocks or timing strobes, with equal access and cycle times. A chip enable function (E) that can be used to place the device into a low-power standby mode is available on all organisations. The 8K x 8 organisations provide an additional Chip Enable for reduced low-power standby mode. Output Enable (\bar{G}) is an enhancement on organisations requiring fast access to data and enhanced bus contention control. The 16x5M series are intended for military applications that demand high performance and superior reliability.

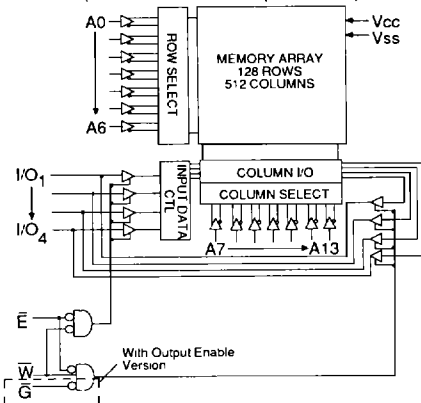
64K x 1



16K x 4 (Separate Inputs and Outputs)



16K x 4 (Without and with Output Enable)



8K x 8 / 8K x 9

